

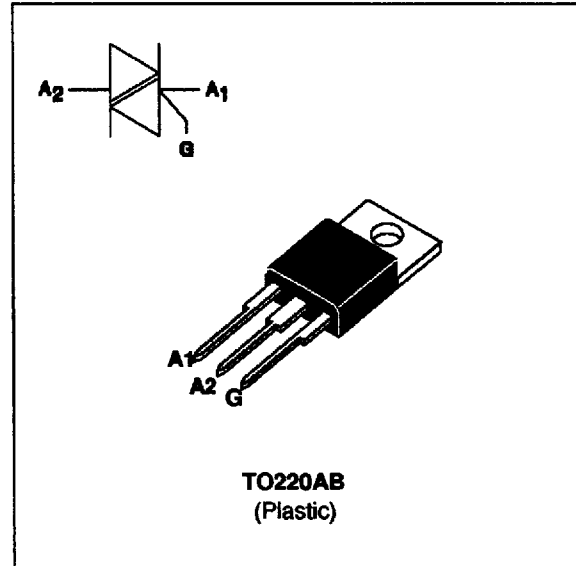
## SNUBBERLESS TRIACS

### FEATURES

- HIGH COMMUTATION :  $(di/dt)_c > 7A/ms$  without snubber
- HIGH SURGE CURRENT :  $I_{TSM} = 80A$
- $V_{DRM}$  UP TO 800V
- BTA Family :  
 INSULATING VOLTAGE = 2500V<sub>(RMS)</sub>  
 (UL RECOGNIZED : E81734)

### DESCRIPTION

The BTA/BTB08 BW/CW triac family are high performance glass passivated chips technology. The SNUBBERLESS™ concept offer suppression of RC network and it is suitable for application such as phase control and static switching on inductive or resistive load.



### ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit	
$I_T(RMS)$	RMS on-state current (360° conduction angle)	BTA	$T_c = 90\text{ °C}$	8	A
		BTB	$T_c = 95\text{ °C}$		
$I_{TSM}$	Non repetitive surge peak on-state current ( $T_j$ initial = 25°C)	$t_p = 8.3\text{ ms}$		85	A
		$t_p = 10\text{ ms}$		80	
$I^2t$	$I^2t$ value	$t_p = 10\text{ ms}$		32	A <sup>2</sup> s
$di/dt$	Critical rate of rise of on-state current Gate supply : $I_G = 500mA$ $di_G/dt = 1A/\mu s$	Repetitive $F = 50\text{ Hz}$		20	A/ $\mu s$
		Non Repetitive		100	
$T_{stg}$ $T_j$	Storage and operating junction temperature range		- 40 to + 150 - 40 to + 125	°C °C	
$T_l$	Maximum lead temperature for soldering during 10 s at 4.5 mm from case		260	°C	

Symbol	Parameter	BTA / BTB08-... BW/CW				Unit
		400	600	700	800	
$V_{DRM}$ $V_{RRM}$	Repetitive peak off-state voltage $T_j = 125\text{ °C}$	400	600	700	800	V

**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
Rth (j-a)	Junction to ambient	60	°C/W
Rth (j-c) DC	Junction to case for DC	BTA	4.4
		BTB	3.3
Rth (j-c) AC	Junction to case for 360° conduction angle ( F= 50 Hz)	BTA	3.3
		BTB	2.5

**GATE CHARACTERISTICS (maximum values)**

PG (AV) = 1W PGM = 10W (tp = 20 μs) IGM = 4A (tp = 20 μs) VGM = 16V (tp = 20 μs).

**ELECTRICAL CHARACTERISTICS**

Symbol	Test Conditions		Quadrant		Suffix		Unit
					BW	CW	
IGT	VD=12V (DC) RL=33Ω	Tj=25°C	I-II-III	MIN	2	1	mA
				MAX	50	35	
VGT	VD=12V (DC) RL=33Ω	Tj=25°C	I-II-III	MAX	1.5		V
VGD	VD=VDRM RL=3.3kΩ	Tj=125°C	I-II-III	MIN	0.2		V
tgt	VD=VDRM IG = 500mA dIG/dt = 3A/μs	Tj=25°C	I-II-III	TYP	2		μs
IL	IG=1.2 IGT	Tj=25°C	I-III	TYP	40	-	mA
			II	TYP	80	-	
			I-III	MAX	-	50	
			II	MAX	-	80	
IH *	IT= 500mA gate open	Tj=25°C		MAX	50	35	mA
VTM *	ITM= 11A tp= 380μs	Tj=25°C		MAX	1.75		V
IDRM IRRM	VDRM Rated VRRM Rated	Tj=25°C		MAX	0.01		mA
		Tj=125°C		MAX	2		
dV/dt *	Linear slope up to VD=67%VDRM gate open	Tj=125°C		MIN	500	250	V/μs
				TYP	750	500	
(di/dt)c *	Without snubber	Tj=125°C		MIN	7	4.5	A/ms
				TYP	14	9	

\* For either polarity of electrode A2 voltage with reference to electrode A1.

ORDERING INFORMATION

Package	$I_T(RMS)$	$V_{DRM} / V_{RRM}$	Sensitivity Specification	
	A	V	BW	CW
BTA (Insulated)	8	400	X	X
		600	X	X
		700	X	X
		800	X	X
BTB (Uninsulated)	8	400	X	X
		600	X	X
		700	X	X
		800	X	X

Fig.1 : Maximum RMS power dissipation versus RMS on-state current ( $F=50Hz$ ).  
(Curves are cut off by  $(di/dt)_c$  limitation)

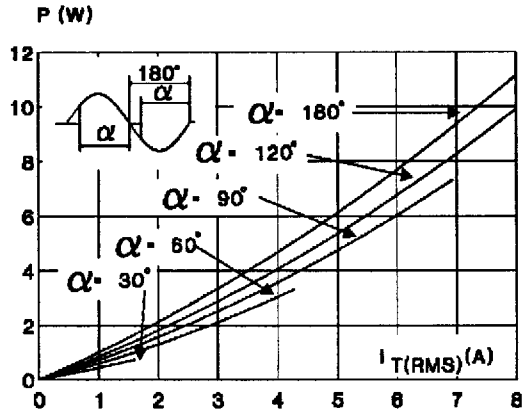


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperatures ( $T_{amb}$  and  $T_{case}$ ) for different thermal resistances heatsink + contact (BTA).

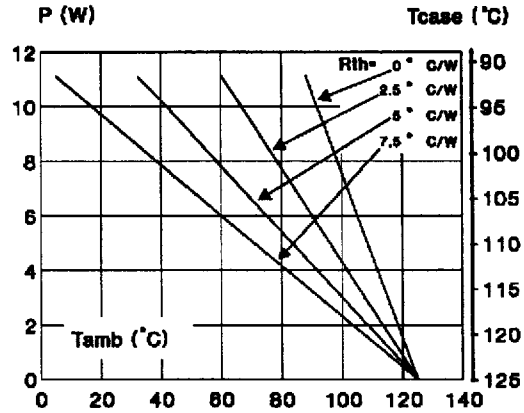


Fig.3 : Correlation between maximum RMS power dissipation and maximum allowable temperatures ( $T_{amb}$  and  $T_{case}$ ) for different thermal resistances heatsink + contact (BTB).

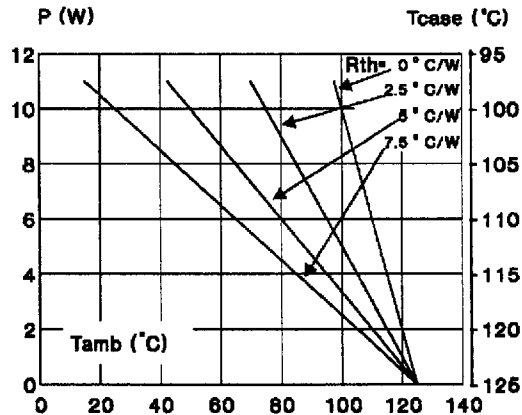
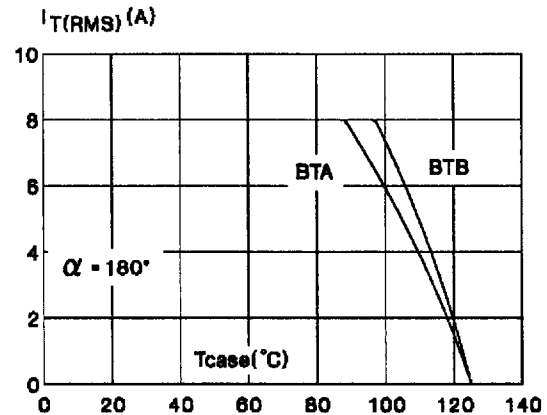


Fig.4 : RMS on-state current versus case temperature.



# BTA08 BW/CW / BTB08 BW/CW

Fig.5 : Relative variation of thermal impedance versus pulse duration.

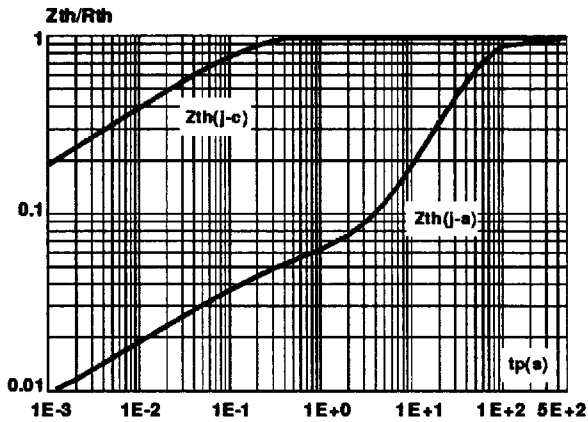


Fig.6 : Relative variation of gate trigger current and holding current versus junction temperature.

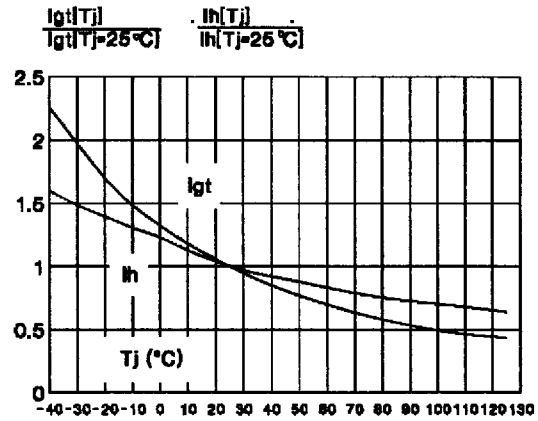


Fig.7 : Non Repetitive surge peak on-state current versus number of cycles.

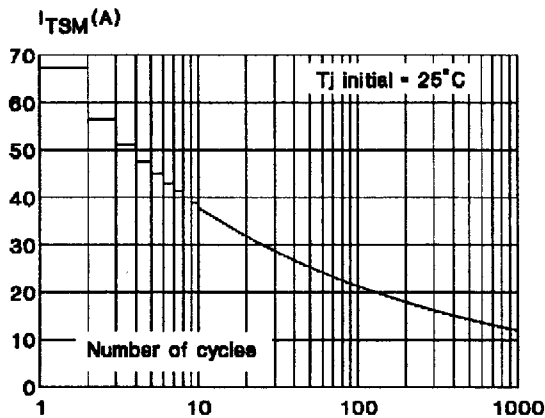


Fig.8 : Non repetitive surge peak on-state current for a sinusoidal pulse with width :  $t \leq 10\text{ms}$ , and corresponding value of  $I^2t$ .

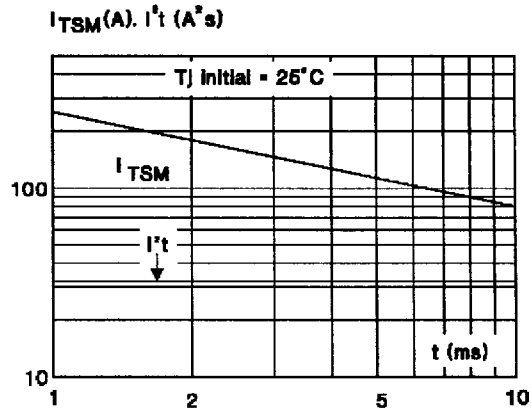
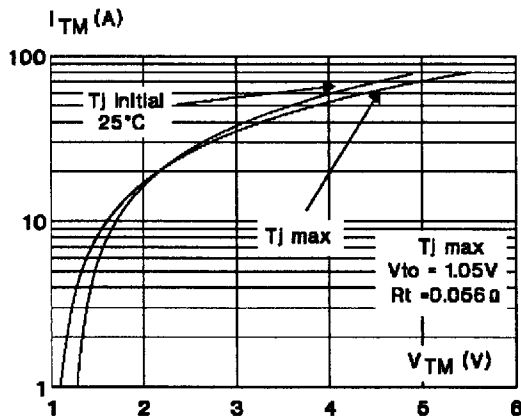
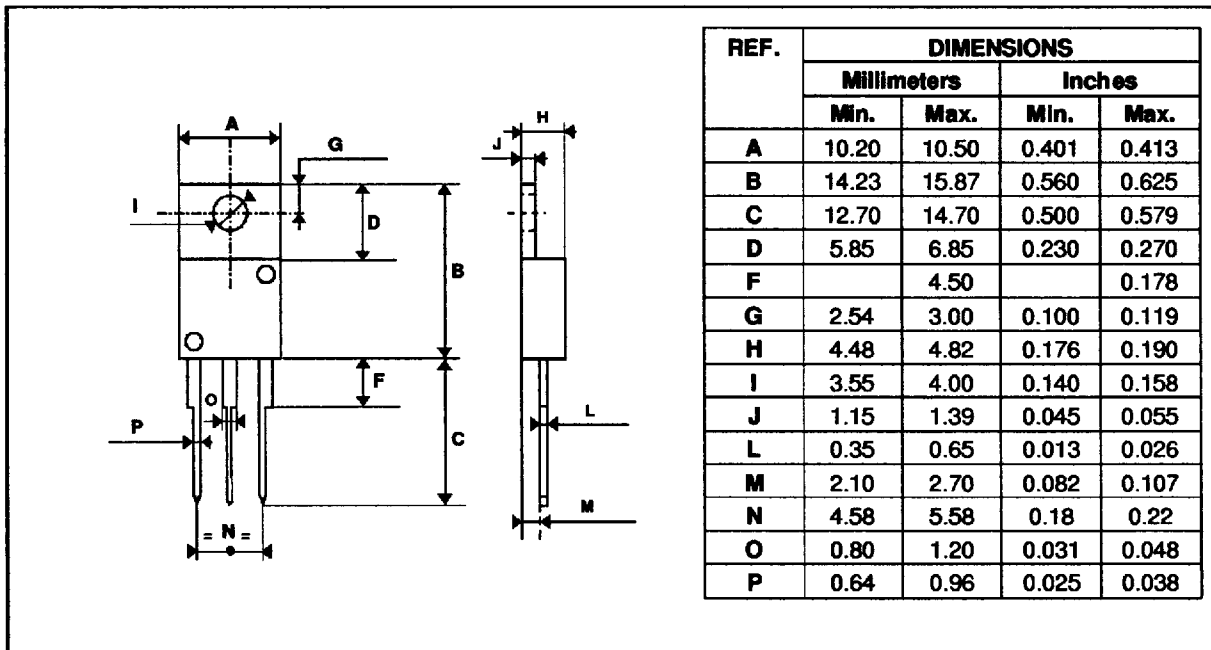


Fig.9 : On-state characteristics (maximum values).



**PACKAGE MECHANICAL DATA**

TO220AB Plastic



Cooling method : C  
 Marking : type number  
 Weight : 2.3 g  
 Recommended torque value : 0.8 m.N.  
 Maximum torque value : 1 m.N.

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